

STAC150V2-350E

RF power transistor: HF/VHF/UHF RF power N-channel MOSFET

Datasheet - production data

Features

- Operating frequencies up to 40.68 MHz
- Excellent thermal stability
- P_{OUT} = 350 W with 17 dB gain @ 40.68 MHz/150 V
- Designed for class E operation
- V_{(BR)DSS} > 700 V
- STAC air cavity packaging technology -STAC[®] package
- In compliance with the 2002/95/EC1 European directive

Description

The STAC150V2-350E is a high voltage Nchannel MOS field-effect RF power transistor especially designed for 150V Industrial RF power class E generators such as PECVD plasma sputtering, flat panel and solar cells manufacturing equipments. STAC150V2-350E benefits from the latest generation of STAC[®] air cavity package which exhibits a 25% lower thermal resistance compared to equivalent ceramic package.



Figure 1. Pin connection



Table 1. Device summary

Order code	Marking	Base qty.	Package	Packaging
STAC150V2-350E	150V2-350 ⁽¹⁾	25 pcs	STAC177B	Plastic tray

1. For more details please refer to Chapter 6: Marking, packing and shipping specifications..

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This is information on a product in full production.

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1 Electrical data

1.1 Maximum ratings

 $(T_{CASE} = 25 \ ^{\circ}C)$

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{(BR)DSS}	Drain source voltage	700	V
V _{GS}	Gate-source voltage	±20	V
TJ	Max. operating junction temperature	200	°C
T _{STG}	Storage temperature	-65 to +150	°C

1.2 Thermal data

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Symbol	Parameter	Value	Unit
R _{thJC} Junction - case thermal resistance		TBD	°C/W



2 Electrical characteristics

 T_{CASE} = +25 °C

2.1 Static

Table 4.	Static						
Symbol		Test conditions		Min	Тур	Max	Unit
V _{(BR)DSS}	$I_{DS} = 250 \mu A$			700			V
I _{DSS}	V _{GS} = 0 V	V _{DS} = 150 V				1	μA
I _{GSS}	V _{GS} = 20 V	$V_{DS} = 0 V$				0.4	μA
V _{TH}	$I_D = 250 \ \mu A$			3		6.5	V
V _{DS(ON)}	V _{GS} = 10 V	I _D = 7.5 A				10	V
G _{FS}	$V_{DS} = TBD V$	I _D = TBD A			TBD		S
C _{ISS}	$V_{GS} = 0 V$	V _{DS} = 150 V	f = 1 MHz		1300		pF
C _{OSS}	$V_{GS} = 0 V$	V _{DS} = 150 V	f = 1 MHz		115		pF
C _{RSS}	$V_{GS} = 0 V$	V _{DS} = 150 V	f = 1 MHz		15		pF

2.2 Dynamic

Symbol	Test conditions		Тур	Max	Unit
P _{OUT}	V _{DD} = 150 V, P _{IN} = 12 W, f = 40.68 MHz	350	500	-	W
Gain	V _{DD} = 150 V, P _{IN} = 12 W, f = 40.68 MHz		16.5	-	dB
Efficiency	V _{DD} = 150 V, P _{OUT} = 500 W, f = 40.68 MHz	60	70	-	%
Load mismatch	V _{DD} = 150 V, P _{OUT} = 500 W, f = 40.68 MHz		65:1	-	VSWR

Table 5. Dynamic (pulse test: 1ms - 10%)



3 Impedance data

Figure 2. Impedance data



Table 6.Impedance values

Frequecy (MHz)	Z _{in}	Z _{dl}
13.56	TBD	TBD
27.12	TBD	TBD
40.68	0.6 - j1.5	11 + j13



4 Typical performance



Figure 3. C_{OSS} capacitance vs. drain-source Figure 4. voltage



Figure 5. C_{ISS} capacitance vs. drain-source voltage







Figure 6. Gain and efficiency vs output power



5 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Dim	mm			inch		
Dim	Min.	Тур.	Max.	Min.	Тур.	Max.
А	5.72		5.97	0.225		0.235
В	6.73		6.99	0.265		0.275
С	21.84		22.10	0.860		0.870
D	28.70		28.96	1.130		1.140
E		28.02			1.103	
F	0.10		0.15	0.004		0.006
G		0.81			0.032	
Н	1.45		1.70	0.057		0.067
I	5.79		6.15	0.228		0.242
J	27.43		28.45	1.080		1.120
К	15.01		15.27	0.591		0.601

 Table 7.
 STAC177B mechanical data





Figure 7. STAC177B mechanical drawing



6 Marking, packing and shipping specifications

Table 8.	Packing and shipping specifications
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Order code	Packaging	Pcs per tray	Dry pack humidity	Lot code
STAC150V2-350E	Plastic tray	25	< 10 %	Not mixed

Figure 8. Marking layout



Table 9. Marking specifications

Symbol	Description	
CZ	Assembly plant	
ххх	Last 3 digits of diffusion lot	
VY	Diffusion plant	
MAR	Country of origin	
CZ	Test and finishing plant	
у	Assembly year	
уу	Assembly week	



7 Revision history

Table 10.Document revision history

Date	Revision	Changes
24-Jan-2013	1	Initial release.



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